

1. Record Nr.	UNINA9910826903003321
Titolo	Emerging nanoelectronic devices / / An Chen, Globalfoundries, USA [and three others]
Pubbl/distr/stampa	Chichester, West Sussex, United Kingdom : , : John Wiley & Sons Inc., , 2015
ISBN	1-118-95826-8 1-118-95825-X 1-322-31759-3
Edizione	[1st ed.]
Descrizione fisica	1 online resource (573 pages) : illustrations (some color)
Disciplina	621.381
Soggetti	Nanoelectronics Nanoelectromechanical systems Nanostructured materials
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di bibliografia	Includes bibliographical references and index.
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